DOCUMENT CHANGE REQUEST

DCR number 1394

Changes required for: General

Originator: Steve Jeffery

Date: 2020/12/03

Date sent: 2020/11/12

Organisation: ESCC Executive

Status: IMPLEMENTED

Title:	Transistors, Power, MOSFET, N-Channel, RAD-HARD, based on Type STRH100N10FSY3		
Number:	5205/021	Issue:	8

Other documents affected:

Page:

15, 16

Paragraph:

2.12.2, Appendix A

Original wording:

IGSS1 Drift Value limit: +15nA
IGSS2 Drift Value limit: -15nA
IDSS Drift Value limit: +4uA
VGS(th) Drift Value limits: -50% / +5%
Characteristics are specified for "Total Gate Charge", "Gate-to-Source Charge" and "Gate-to-Drain Charge" (Qg, Qgs and Qgd)

Proposed wording:

IGSS1 Drift Value limit: +20nA
IGSS2 Drift Value limit: -20nA
IDSS Drift Value limit: -
VGS(th) Drift Value limits: -50% / +10%
Qg, Qgs and Qgd removed from the table and associated Agreed Deviation in Appendix A is deleted.

See attached MSWord file of 5205/021 Draft 9A, where all proposed changes are highlighted in yellow.

Justification:

Note: this DCR has been raised by the ESCC T.W. on behalf of the ESCC Qualified mfr STMicroelectronics.

For 5205/021 (STRH100N10), ST wish to align some of the Drift Value limits for Electrical Measurements for Total Dose Radiation Testing with those defined in ESCC 5205/026 because the N-Channel rad-hard power MOSFETs in both these specs are similar. (These proposed changes are considered by the T.W. to be technically acceptable.)

Attachments:
escc5205021iss9drafta_for_dcr_review.docx
Modifications:
N/A
Approval signature:
Date signed:
2020-12-03